What is claimed is:

1. A method for multi-layer alignment of a semiconductor substrate with alignment marks, comprising:

forming a first layer with first alignment marks on the semiconductor substrate, wherein the first alignment marks are separated parallelly by a predetermined distance;

forming a second layer with second alignment marks on the first layer, wherein the second alignment marks are separated parallelly by a predetermined distance;

measuring the shift distance of each first alignment mark to calculate a first midpoint between the first alignments;

measuring the shift distance of each second alignment mark to calculate a second midpoint between the second alignments; and

calculating a third midpoint acting as a datum point between the fist midpoint and the second midpoint.

2. The method for multi-layer alignment as claimed in claim 1, wherein the second alignment marks and the first alignment marks overlap partially.

3. A method for multi-layer alignment for a semiconductor substrate with alignment marks, comprising:

forming a first layer with first alignment marks on the semiconductor substrate, wherein the first alignment marks are separated parallelly by a predetermined distance;

forming a second layer with second alignment marks on the first layer, wherein the second alignment marks are separated parallelly by a predetermined distance, and the second alignment marks and the first alignment marks are alternately disposed;

measuring the shift distance of each first alignment mark to calculate a first midpoint between the first alignments;

measuring the shift distance of each second alignment mark to calculate a second midpoint between the second alignments; and

calculating a third midpoint acting as a datum point between the fist midpoint and the second midpoint.

4. The method for multi-layer alignment as claimed in claim 3, wherein the second alignment marks and the first alignment marks overlap partially.

5. A marks for multi-layer alignment of a semiconductor substrate, comprising:

a first layer with first alignment marks, wherein the first alignment marks are separated parallelly by a predetermined distance; and

a second layer with second alignment marks, wherein the second alignment marks are separated parallelly by a predetermined distance, the second alignment marks and the first alignment marks are alternately disposed, and overlap completely.